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**03500.017774**APPLICATION NO  
**10/535,452**APPLICANTS  
**MIKI OGAWA, ET AL.**FILING DATE  
**May 19, 2005**GROUP  
**1765**

## U. S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		<b>5,244,828</b>	<b>09/1993</b>	<b>Okada, et al.</b>	<b>437</b>	<b>81</b>	
		<b>5,240,558</b>	<b>08/1993</b>	<b>Kawasaki, et al.</b>	<b>156</b>	<b>659.1</b>	
		<b>5,369,873</b>	<b>12/1994</b>	<b>Walters, et al.</b>	<b>29</b>	<b>599</b>	
		<b>2001/0042502</b>	<b>11/2001</b>	<b>Shih, et al.</b>	<b>117</b>	<b>3</b>	
		<b>2002/0167013</b>	<b>11/2002</b>	<b>Iwasaki, et al.</b>	<b>257</b>	<b>79</b>	
		<b>2003/0175472</b>	<b>09/2003</b>	<b>Den, et al.</b>	<b>428</b>	<b>66.6</b>	
		<b>6,027,796</b>	<b>02/2000</b>	<b>Kondoh, et al.</b>	<b>428</b>	<b>312.8</b>	
		<b>6,602,620</b>	<b>08/2003</b>	<b>Kikitsu, et al.</b>	<b>428</b>	<b>694 T</b>	

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
		<b>5-55545</b>	<b>03/1993</b>	<b>Japan</b>			<b>Abstract</b>
		<b>0 851 506</b>	<b>07/1998</b>	<b>Europe</b>			
		<b>11-31862</b>	<b>02/1999</b>	<b>Japan</b>			<b>Abstract</b>
		<b>11-251334</b>	<b>09/1999</b>	<b>Japan</b>			<b>Abstract</b>
		<b>58-142523</b>	<b>08/1983</b>	<b>Japan</b>			<b>Abstract</b>

## OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

	<b>M. Jacobs, et al., "Unbalanced Magnetron Sputtered Si-Al Coatings: Plasma Conditions and Film Properties Versus Sample Bias Voltage", Surface and Coatings Technology, 116-119, pp. 735-741 (1999).</b>
	<b>C.D. Adams, et al., "Transition from Lateral to Transverse Phase Separation During Film Co-Deposition", Appl. Phys. Lett., 59 (20), pp. 2535-2537 (November 11, 1991).</b>
	<b>M. Atzmon, et al., "Phase Separation During Film Growth", J. Appl. Phys. 72 (2), pp. 442-446 (July 15, 1992).</b>

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		2004/0048092	03/2004	Yasui, et al.	428	642	
		2004/0033339	02/2004	Fukutani, et al.	428	137	
		2004/0043208	03/2004	Fukutani, et al.	428	304.4	
		5,068,152	11/1991	Maro, et al.	428	408	
		2004/0166376	08/2004	Kirino, et al.	428	694	
		6,730,421	05/2004	Kirino, et al.	428	694	
		7,282,268	10/2007	Fukutani, et al.	428	446	

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
		2001-261376	09/2001	Japan			Abstract
		9-157062	06/1997	Japan			Abstract
		WO 01/71394	09/2001	PCT			No
		2000-327491	11/2000	Japan			Abstract
		2-139714	05/1990	Japan			Abstract
		WO 03/069677	08/2003	PCT			

## OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

	C.D. Adams, et al., "Monte Carlo Simulation of Phase Separation During Thin-Film Codeposition", J. Appl. Phys., 74 (3), pp. 1707-1715 (August 1, 1993).
	C.D. Adams, et al., "Phase Separation During Co-Deposition of Al-Ge Thin Films", Journal of Materials Research, Vol. 7, No. 3, p. 653 (March 1992).
	N. E. Sluchanko, et al., "Late Stages of Phase Separation in Al <sub>1-x</sub> Si <sub>x</sub> Solid Solutions", Physical Review B, Vol. 53, No. 17, pp. 11 304-11 306 (May 1, 1996).

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